Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT186A (TO-220F) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

2. Features and benefits

- · High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Less sensitive gate for improved noise immunity
- · Triggering in all four quadrants
- Isolated package

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute	maximum rating					
V_{DRM}	repetitive peak off-state voltage			600		V
I _{T(RMS)}	RMS on-state current	full sine wave; T _h ≤ 38 °C; Fig. 1; Fig. 2; Fig. 3	16		А	
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	155		А	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-;}$ $T_j = 25 \text{ °C; Fig. 7}$	-	8	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	10	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	22	70	mA

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		Ν
3	G	gate		T2 T1
mb	n.c.	mounting base; isolated		sym051

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BT139X-600F	TO220F	BT139X-600F,127	Tube	50	SOT186A	14-Nov-2013
BT139X-600F/DG		BT139X-600F/DG,127	Tube	50	SOT186A (Halogen free)	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes	
	Assembly factory: d	Assembly factory: A
BT139X-600F	BT139X 600F PJdxxxx xx	BT1396X 600F PJAxxxx xx
BT139X-600F/DG	BT139X 600FDG PJdxxxx xx	BT139X 600FDG PJAxxxx xx

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; T _h ≤ 38 °C; Fig 1; Fig 2; Fig 3	16	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig 4; Fig 5	155	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	170	Α
l ² t	I ² t for fusing	t _p = 10 ms; SIN	120	A ² s
dl _⊤ /dt	rate of rise of on-state	I _G = 50 mA; T2+ G+	50	A/µs
	current	I _G = 50 mA; T2+ G-	50	A/µs
		I _G = 50 mA; T2- G-	50	A/µs
		I _G = 140 mA; T2- G+	10	A/µs
I _{GM}	peak gate current		2	А
P_GM	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

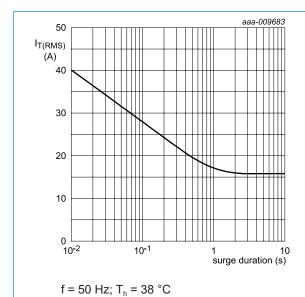


Fig. 1. RMS on-state current as a function of surge duration; maximum values

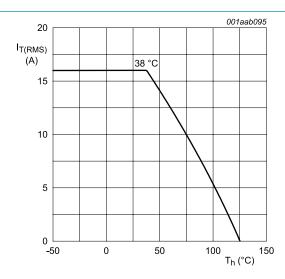
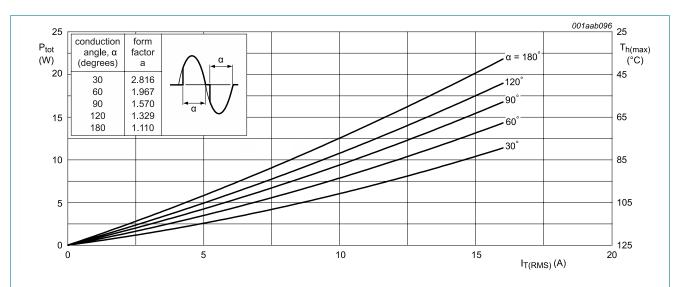


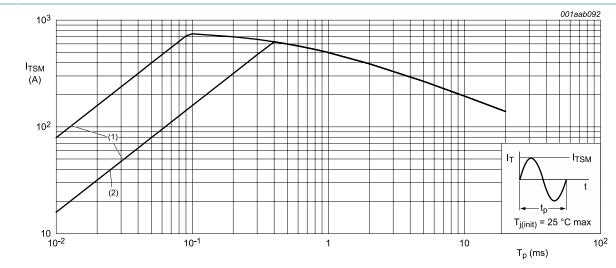
Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values



 α = conduction angle

a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms}$

- $(1) dI_{T}/dt limit$
- (2) T2- G+ quadrant limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

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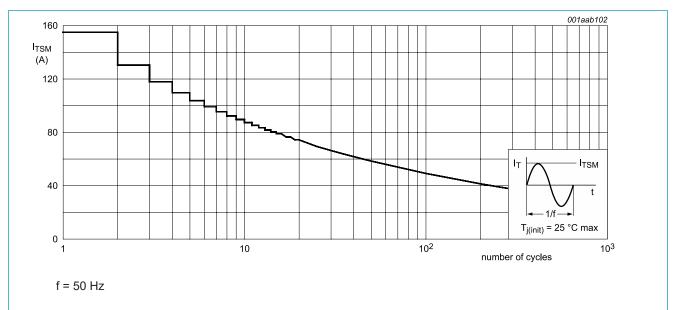


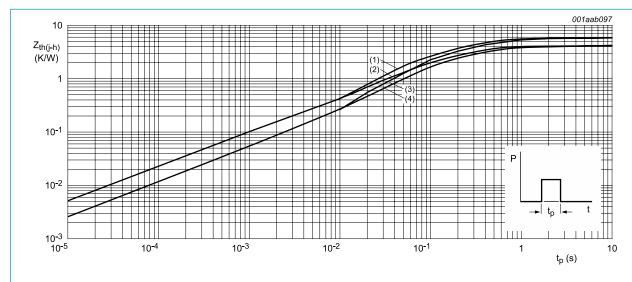
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	full or half cycle; with heatsink compound; Fig 6	-	-	4	K/W
	heatsink	full or half cycle; without heatsink compound; Fig 6	-	-	5.5	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

10. Isolation characteristics

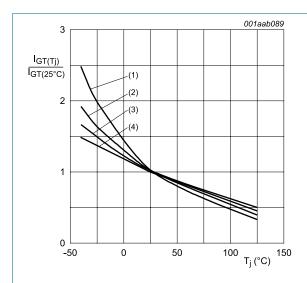
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; $T_h = 25$ °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	5	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	8	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	10	25	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } Fig. 7$	-	22	70	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	7	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	20	60	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	8	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	10	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	6	45	mA
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I_D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	50	250	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 95 \text{ °C}; dl_{com}/dt = 7.2 \text{ A/}$ ms; $I_T = 16 \text{ A}; gate open circuit}$	-	20	-	V/µs
\mathbf{t}_{gt}	gate-controlled turn-on time	$V_D = 600 \text{ V}; I_{TM} = 20 \text{ A}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

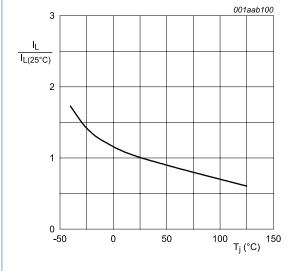


Fig. 8. Normalized latching current as a function of junction temperature

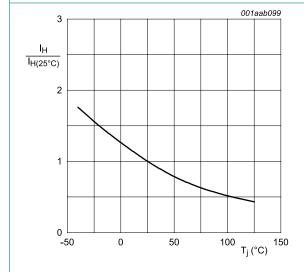
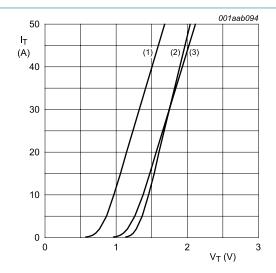


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.195 V; R_s = 0.018 Ω (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

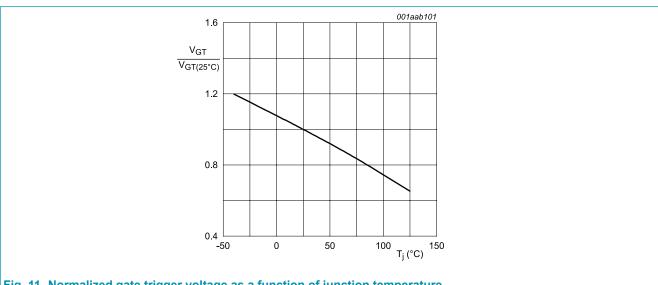
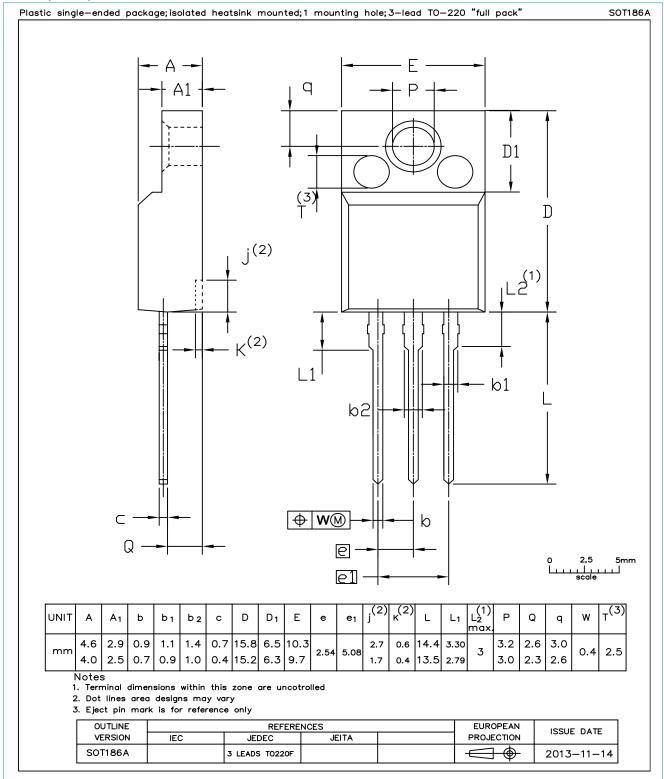


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline

Assembly factory: d & A



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For more information, please visit: http://www.ween-semi.com For sales office addresses, please send an email to: salesaddresses@ween-semi.com Date of release: 25 September 2024

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